

IN THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application

Listing of Claims:

1-14. (Cancelled)

15. (Previously presented) A light-emitting diode comprising:

a substrate made of group III-V nitride semiconductor;

a first n-type semiconductor layer containing indium and formed over a main surface of the substrate;

a light-emitting layer formed over the first n-type semiconductor layer;

a second n-type semiconductor layer formed between the substrate and the first n-type semiconductor layer;

a third n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer; and

a fourth n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer.

16. (Previously presented) The diode of claim 15,

wherein the fourth n-type semiconductor layer is made of a compound whose general formula is represented by $\text{Al}_e\text{Ga}_{1-e}\text{N}$ ($0 \leq e < 1$).

17. (Previously presented) The diode of claim 16,

wherein the fourth n-type semiconductor layer is a cladding layer.

18. (Previously presented) The diode of claim 17,
wherein the cladding layer has a thickness of 5 to 200 nm inclusive.

19. (Cancelled)

20. (Previously Presented) An illuminating device comprising multiple light-emitting
diodes,

wherein the diodes including:

a substrate made of group III-V nitride semiconductor;

a first n-type semiconductor layer containing indium and formed over a main surface of
the substrate; and

a light-emitting layer formed over the first n-type semiconductor layer.

21. (Cancelled)